

SuperMOS –PDFN5*6-8L 30V BV_{DSS} 10m Ω $R_{DS(on)}$ 32A I_D , N-channel MOSFET

1. Description

The ESN6204 is N-Channel enhancement MOS Field Effect Transistor. Uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. Device is suitable for use in DC-DC conversion, power switch and charging circuit. Standard Product ESN6204 is Pb-free.

2. Features

- 30V, $R_{DS(ON)}=10m\Omega(Typ)$, $V_{GS}=10V$
- $R_{DS(ON)}=13.5m\Omega(Typ)$, $V_{GS}=4.5V$
- Use trench MOSFET technology
- High density cell design for low $R_{DS(on)}$
- Material: Halogen free
- Reliable and rugged
- Avalanche Rated
- Low leakage current

3. Applications

- PWM applications
- Load switch
- Power management in portable/desktop PCs
- DC/DC conversion

100% UIS TESTED

4. Ordering Information

Part Number	Package	Marking	Material	Packing	Quantity per reel	Flammability Rating	Reel Size
ESN6204	PDFN5*6-8L	ESN6204/lot	Halogen free	Tape & Reel	5,000 PCS	UL 94V-0	13 inches

Table-1 Ordering information

5. Pin Configuration and Functions


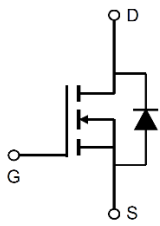
Pin	Function	Outline	Circuit Diagram
1/2/3	Source		
4	Gate		
5/6/7/8	Drain		

Table-2 Pin configuration

6. Specification

Absolute Maximum Rating & Thermal Characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		BV_{DSS}	30	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	$T_C=25^\circ\text{C}$	I_D	32	A
	$T_C=75^\circ\text{C}$		24	
Maximum Power Dissipation	$T_C=25^\circ\text{C}$	P_D	31	W
	$T_C=75^\circ\text{C}$		19	
Pulsed Drain Current		I_{DM}	120	A
Avalanche Current, Single Pulsed ^a		I_{AS}	17	A
Avalanche Energy, Single Pulsed ^a		E_{AS}	43.4	mJ
Operating Junction Temperature		T_J	150	°C
Lead Temperature		T_L	260	°C
Storage Temperature Range		T_{stg}	-55 to 150	°C

Thermal resistance ratings

Single Operation					
Parameter		Symbol	Typical	Maximum	Unit
Junction-to-Case Thermal Resistance	$t \leq 10 \text{ s}$	$R_{\theta JC}$	3.3	4	°C/W

Note:

a: EAS condition: $T_J=25^\circ\text{C}, V_{DD}=30\text{V}, V_G=10\text{V}, L=0.3\text{mH}, R_g=25\Omega$

Electrical Characteristics

At TA = 25°C unless otherwise specified

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	30			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=30V, V_{GS}=0V$			1.0	μA
Gate-to-source Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 20V$			± 100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	1.0	1.5	2.4	V
Drain-to-source On-resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=20A$		10	19	m Ω
		$V_{GS}=4.5V, I_D=15A$		13.5	26	
Forward Trans conductance	g_{FS}	$V_{DS}=5.0V, I_D=20A$			50	S
CHARGES, CAPACITANCES AND GATE RESISTANCE						
Input Capacitance	C_{ISS}	$V_{GS}=0V, f=1MHz, V_{DS}=15V$		512		pF
Output Capacitance	C_{OSS}			225		
Reverse Transfer Capacitance	C_{RSS}			22		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS}=10V, V_{DS}=15V, I_D=20A$		8		nC
Gate-to-Source Charge	Q_{GS}			2		
Gate-to-Drain Charge	Q_{GD}			1.5		
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	$t_{d(ON)}$	$V_{GS}=10V, V_{DS}=15V, R_L=1.5\Omega, R_{GEN}=3\Omega$		4.4		ns
Rise Time	t_r			7.9		
Turn-Off Delay Time	$t_{d(OFF)}$			15.6		
Fall Time	t_f			3.5		
BODY DIODE CHARACTERISTICS						
Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=1.0A$	0.45		1.2	V

7. Typical Characteristic

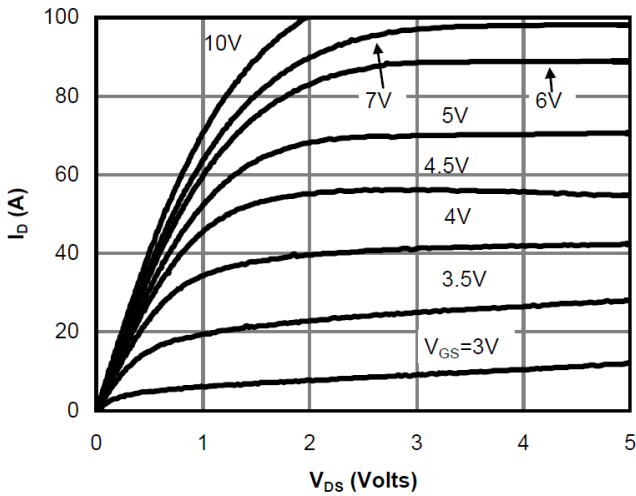


Fig 1: On-Region Characteristics

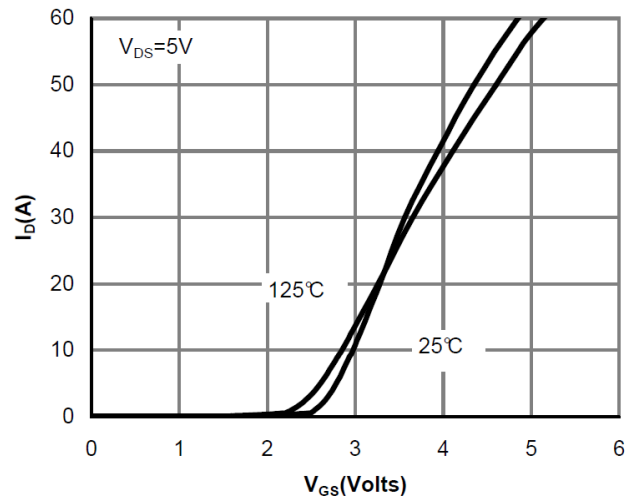


Figure 2: Transfer Characteristics

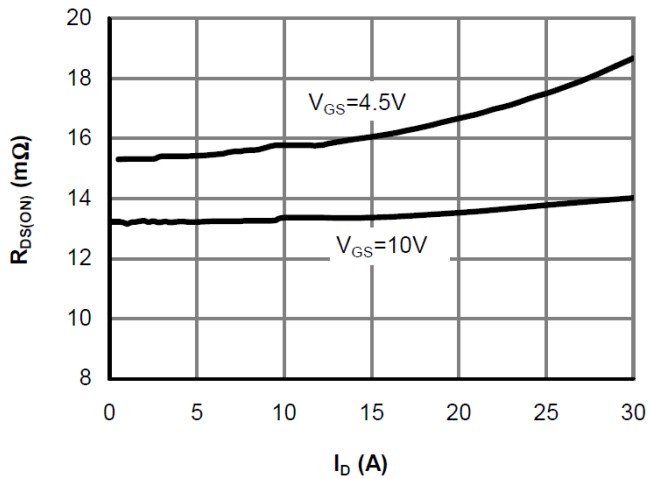


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

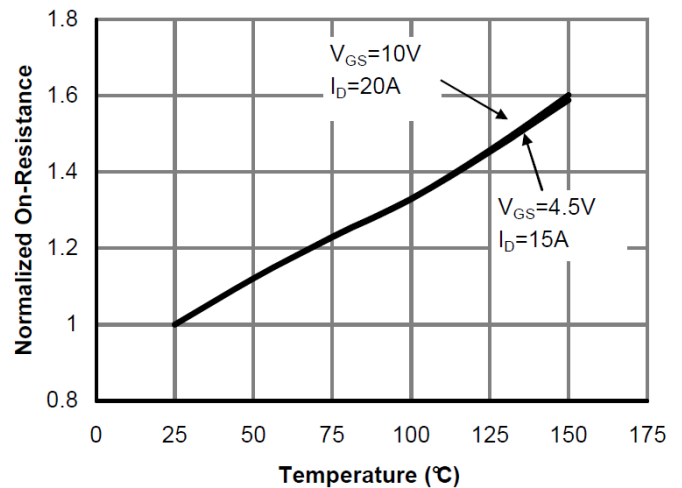


Figure 4: On-Resistance vs. Junction Temperature

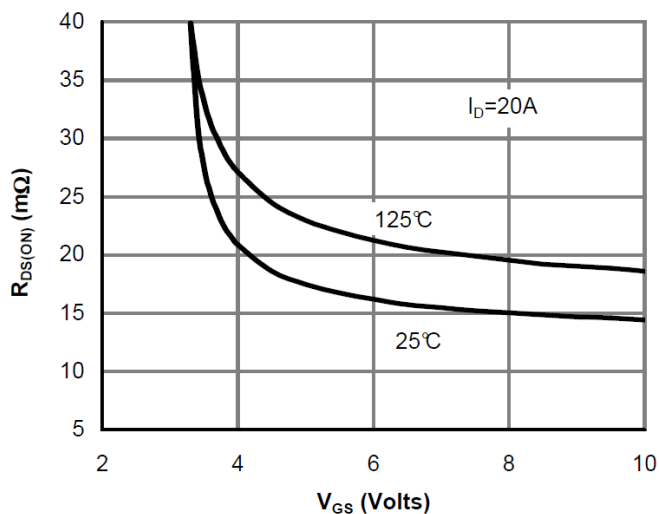


Figure 5: On-Resistance vs. Gate-Source Voltage

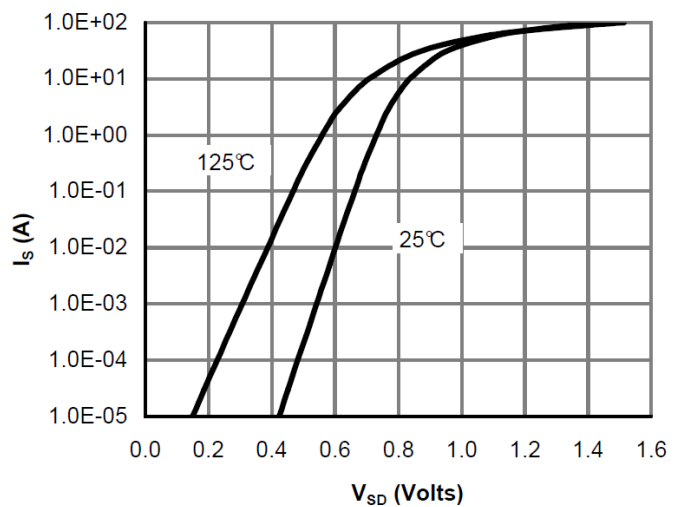


Figure 6: Body-Diode Characteristics

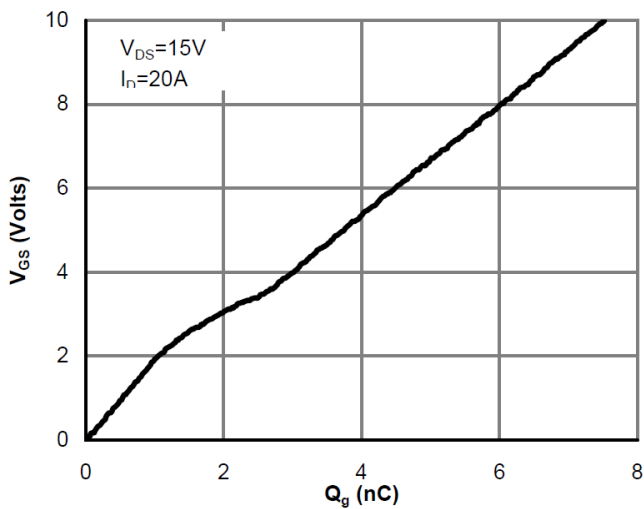


Figure 7: Gate-Charge Characteristics

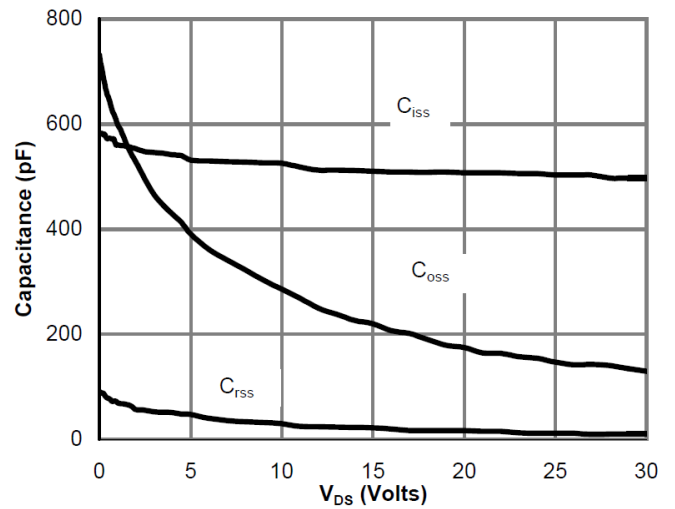


Figure 8: Capacitance Characteristics

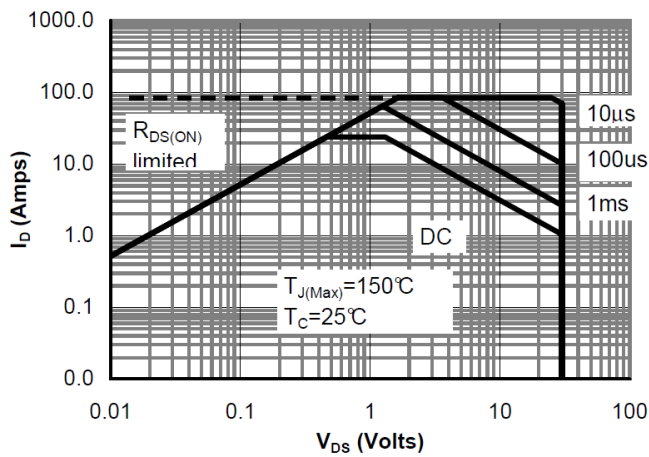


Figure 9: Maximum Forward Biased Safe Operating Area

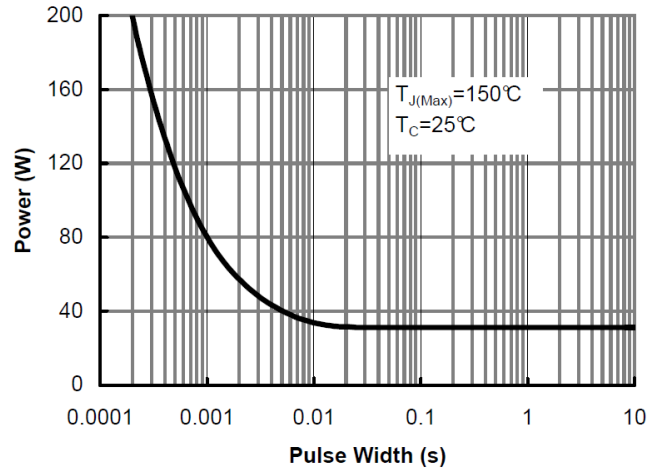


Figure 10: Single Pulse Power Rating Junction-to-Case

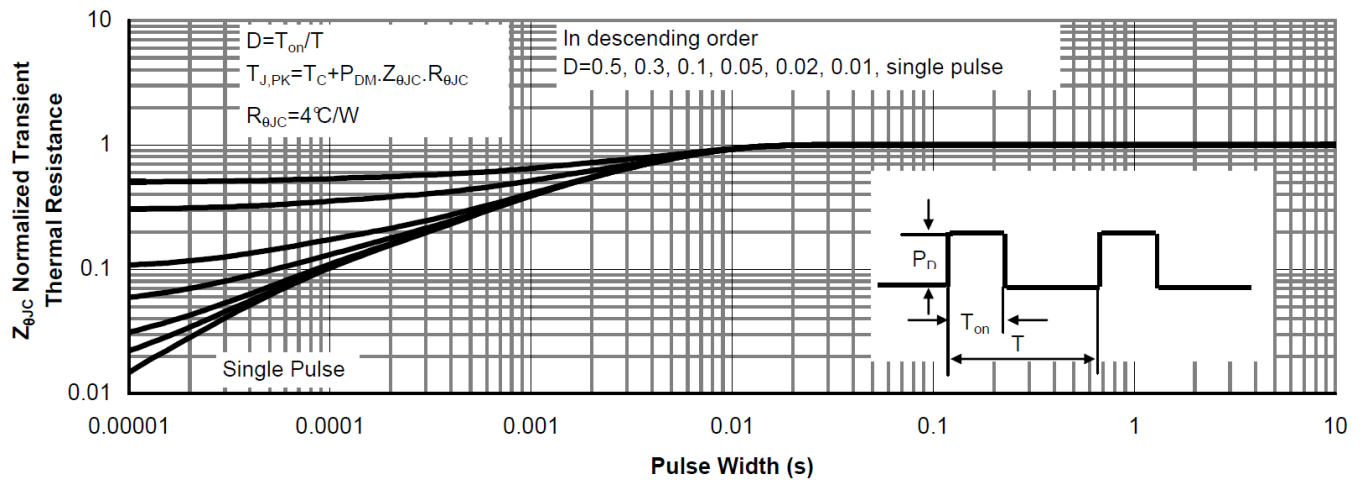
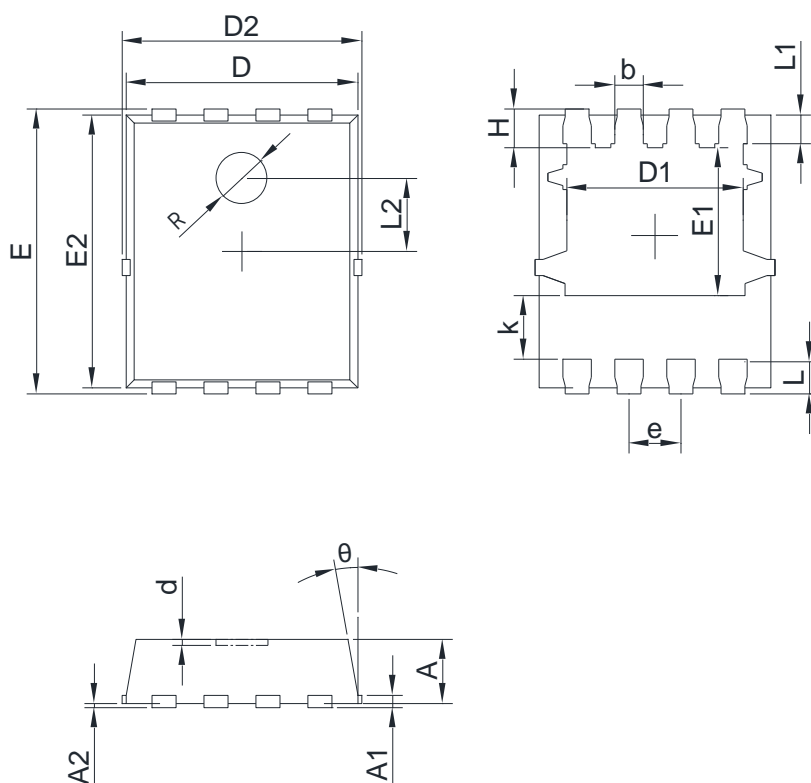


Figure 11: Normalized Maximum Transient Thermal Impedance

8. Dimension (PDFN5*6-8L)



Unit: mm

COMMON DIMENSIONS: UNITS OF MEASURE=MILLIMETER

SYMBOL	MILLIMETER			SYMBOL	MILLIMETER		
	MIN	Typ.	MAX		MIN	Typ.	MAX
A	0.900	1.000	1.100	e	1.270 TYP.		
A1	0.254 REF			l	0.534	0.610	0.686
A2	0~0.05			L1	0.424	0.500	0.576
D	4.824	4.900	4.976	L2	1.800 REF.		
D1	3.910	4.010	4.110	k	1.190	1.290	1.390
D2	4.924	5.000	5.076	H	0.549	0.625	0.701
E	5.924	6.000	6.076	θ	8°	10°	12°
E1	3.375	3.475	3.575	R	1.100	1.200	1.300
E2	5.674	5.750	5.826	d			0.100
b	0.350	0.400	0.450				

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